

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







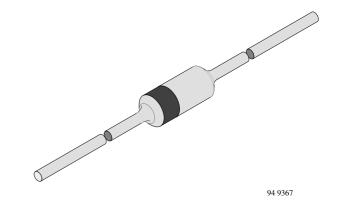




Silicon Epitaxial Planar Z-Diodes

Features

- Very sharp reverse characteristic
- Low reverse current level
- Very high stability
- Low noise
- Available with tighter tolerances



Applications

Voltage stabilization

Order Instruction

Type	Ordering Code	Remarks
BZX55C2V4	BZX55C2V4-TAP	Ammopack

Absolute Maximum Ratings

 $T_i = 25^{\circ}C$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Power dissipation	I=4 mm, T _L =25 °C		P_V	500	mW
Z-current			Ι _Ζ	P_V/V_Z	mΑ
Junction temperature			T _i	175	°C
Storage temperature range			T _{sta}	<i>–</i> 65+175	°C

Maximum Thermal Resistance

 $T_i = 25^{\circ}C$

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	I=4 mm, T _L =constant	R_{thJA}	300	K/W

Electrical Characteristics

 $T_i = 25^{\circ}C$

Parameter	Test Conditions	Type	Symbol	Min	Тур	Max	Unit
Forward voltage	I _F =200mA		V_{F}			1.5	٧

Document Number 85605 Rev. 5, 12-Mar-01



Туре	V_{Znom}		I _{ZT} for V _{ZT} and i	ziT	r _{zik} at	I _{ZK}	I_R and I_R at V_R			TK _{VZ}
BZX55C	V	mA	V 1)	Ω	Ω	mA	μA	μ A ²⁾	V	%/K
2V4	2.4	5	2.28 to 2.56	< 85	< 600	1	< 50	< 100	1	-0.09 to -0.06
2V7	2.7	5	2.5 to 2.9	< 85	< 600	1	< 10	< 50	1	-0.09 to -0.06
3V0	3.0	5	2.8 to 3.2	< 85	< 600	1	< 4	< 40	1	-0.08 to -0.05
3V3	3.3	5	3.1 to 3.5	< 85	< 600	1	< 2	< 40	1	-0.08 to -0.05
3V6	3.6	5	3.4 to 3.8	< 85	< 600	1	< 2	< 40	1	-0.08 to -0.05
3V9	3.9	5	3.7 to 4.1	< 85	< 600	1	< 2	< 40	1	-0.08 to -0.05
4V3	4.3	5	4.0 to 4.6	< 75	< 600	1	< 1	< 20	1	-0.06 to -0.03
4V7	4.7	5	4.4 to 5.0	< 60	< 600	1	< 0.5	< 10	1	-0.05 to +0.02
5V1	5.1	5	4.8 to 5.4	< 35	< 550	1	< 0.1	< 2	1	-0.02 to +0.02
5V6	5.6	5	5.2 to 6.0	<25	< 450	1	< 0.1	< 2	1	-0.05 to +0.05
6V2	6.2	5	5.8 to 6.6	< 10	< 200	1	< 0.1	< 2	2	0.03 to 0.06
6V8	6.8	5	6.4 to 7.2	< 8	< 150	1	< 0.1	< 2	3	0.03 to 0.07
7V5	7.5	5	7.0 to 7.9	< 7	< 50	1	< 0.1	< 2	5	0.03 to 0.07
8V2	8.2	5	7.7 to 8.7	< 7	< 50	1	< 0.1	< 2	6.2	0.03 to 0.08
9V1	9.1	5	8.5 to 9.6	< 10	< 50	1	< 0.1	< 2	6.8	0.03 to 0.09
10	10	5	9.4 to 10.6	< 15	< 70	1	< 0.1	< 2	7.5	0.03 to 0.1
11	11	5	10.4 to 11.6	< 20	< 70	1	< 0.1	< 2	8.2	0.03 to 0.11
12	12	5	11.4 to 12.7	< 20	< 90	1	< 0.1	< 2	9.1	0.03 to 0.11
13	13	5	12.4 to 14.1	< 26	< 110	1	< 0.1	< 2	10	0.03 to 0.11
15	15	5	13.8 to 15.6	< 30	< 110	1	< 0.1	< 2	11	0.03 to 0.11
16	16	5	15.3 to 17.1	< 40	< 170	1	< 0.1	< 2	12	0.03 to 0.11
18	18	5	16.8 to 19.1	< 50	< 170	1	< 0.1	< 2	13	0.03 to 0.11
20	20	5	18.8 to 21.2	< 55	< 220	1	< 0.1	< 2	15	0.03 to 0.11
22	22	5	20.8 to 23.3	< 55	< 220	1	< 0.1	< 2	16	0.04 to 0.12
24	24	5	22.8 to 25.6	< 80	< 220	1	< 0.1	< 2	18	0.04 to 0.12
27	27	5	25.1 to 28.9	< 80	< 220	1	< 0.1	< 2	20	0.04 to 0.12
30	30	5	28 to 32	< 80	< 220	1	< 0.1	< 2	22	0.04 to 0.12
33	33	5	31 to 35	< 80	< 220	1	< 0.1	< 2	24	0.04 to 0.12
36	36	5	34 to 38	< 80	< 220	1	< 0.1	< 2	27	0.04 to 0.12
39	39	2.5	37 to 41	< 90	< 500	0.5	< 0.1	< 5	30	0.04 to 0.12
43	43	2.5	40 to 46	< 90	< 600	0.5	< 0.1	< 5	33	0.04 to 0.12
47	47	2.5	44 to 50	< 110	< 700	0.5	< 0.1	< 5	36	0.04 to 0.12
51	51	2.5	48 to 54	< 125	< 700	0.5	< 0.1	< 10	39	0.04 to 0.12
56	56	2.5	52 to 60	< 135	< 1000	0.5	< 0.1	< 10	43	0.04 to 0.12
62	62	2.5	58 to 66	< 150	< 1000	0.5	< 0.1	< 10	47	0.04 to 0.12
68	68	2.5	64 to 72	< 200	< 1000	0.5	< 0.1	< 10	51	0.04 to 0.12
75	75	2.5	70 to 79	< 250	< 1500	0.5	< 0.1	< 10	56	0.04 to 0.12

 $^{1)}$ Tighter tolerances available on request: BZX55A... \pm 1% of V_{Znom} BZX55B... \pm 2% of V_{Znom} BZX55F... \pm 3% of V_{Znom} at T_j= 150 $^{\circ}$ C



Characteristics $(T_j = 25^{\circ}C \text{ unless otherwise specified})$

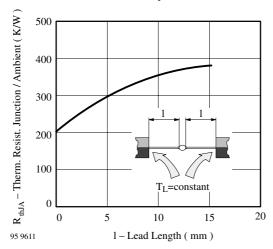


Figure 1. Thermal Resistance vs. Lead Length

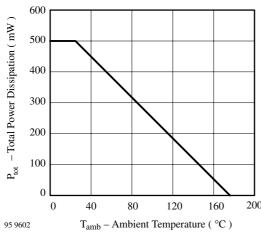


Figure 2. Total Power Dissipation vs. Ambient Temperature

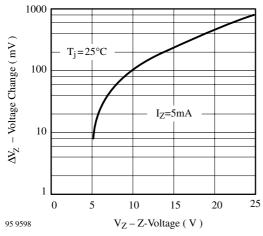


Figure 3. Typical Change of Working Voltage under Operating Conditions at T_{amb}=25 °C

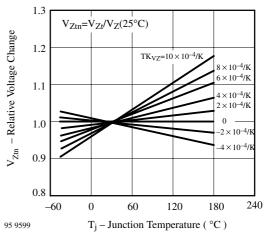


Figure 4. Typical Change of Working Voltage vs.
Junction Temperature

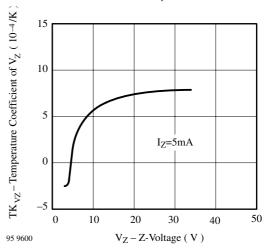


Figure 5. Temperature Coefficient of Vz vs. Z-Voltage

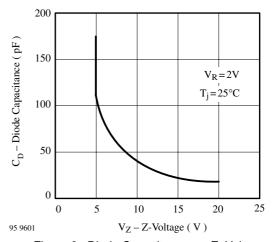


Figure 6. Diode Capacitance vs. Z-Voltage



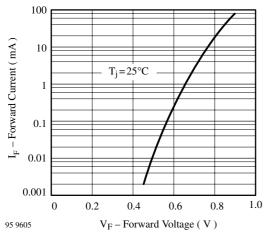


Figure 7. Forward Current vs. Forward Voltage

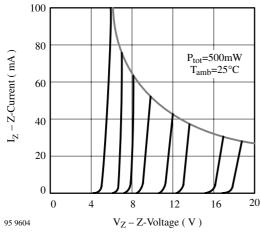


Figure 8. Z-Current vs. Z-Voltage

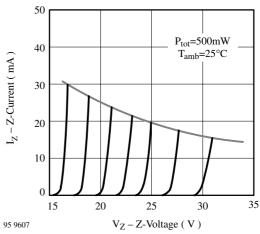


Figure 9. Z-Current vs. Z-Voltage

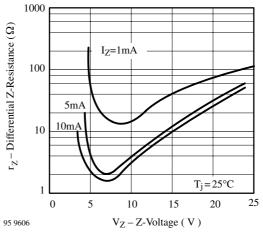


Figure 10. Differential Z-Resistance vs. Z-Voltage

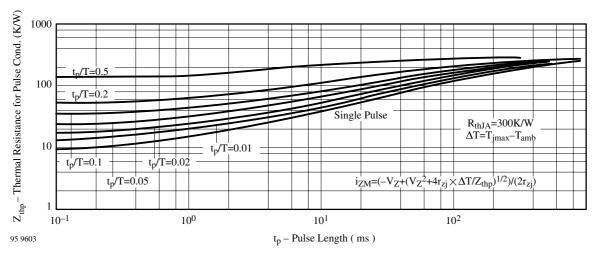


Figure 11. Thermal Response



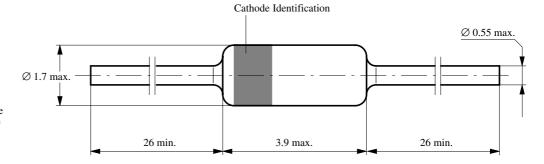


Dimensions in mm



94 9366

Standard Glass Case 54 A 2 DIN 41880 JEDEC DO 35 Weight max. 0.3 g





Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany Telephone: 49 (0) 7131 67 2831, Fax number: 49 (0) 7131 67 2423